



# LITAO3 WAFER FOR SAW DEVICE

- 1 This specification is used for 3" Lithium Tantalate wafer (SAW grade).
- 2 Growth method for Lithium Tantalate is to be Czochralsky pulled and it is a single crystal.
- 3 General LiTaO3 Wafer Requirements
  - 3.1 Wafer Diameter --  $76.2 \pm 0.5$  mm.
  - 3.2 Thickness --  $0.50 \pm 0.05$  mm,  $0.35 \pm 0.05$ , or other size if specified.
  - 3.3 Bow --  $< 50$  microns (see Figure #3).
  - 3.4 Taper --  $< 0.025$  mm (see Figure #4).
  - 3.5 Wafer Orientation -- To be as requested  $\pm 0.2$  degrees ( $\pm 12$  minutes), unless specified .
  - 3.6 Identification flat position and length is to be as follows:
    - 3.6.1 Primary Flat Location -- Must be within  $\pm 0.1$  degrees ( $\pm 6$  minutes), unless specified .
    - 3.6.2 Primary Flat Length -- From 20 to 24 mm, unless specified.
    - 3.6.3 Secondary Flat Location(s) -- Must be within  $\pm 2.5$  degrees, as illustrated in Figure #2.
    - 3.6.4 Secondary Flat Length -- From 8 to 12 mm.
  - 3.7 Surface Polish Quality
    - 3.7.1 Cleanliness -- No stains or residues on either side when inspected under a collimated light
    - 3.7.2 Front surface must be free of scratches, pits, dimples, cracks, "orange peel", smudges, fingerprints, saw marks, and unpolished areas. Typically referred to as "mirror polish".
    - 3.7.3 Backside Polish -- Lapped with GC1100# (W14) diamond sand and etched.
    - 3.7.4 Edge Chips -- Not to exceed 0.75 mm in diameter.
    - 3.7.5 Edge Bevel -- To extend inward from the wafer edge 0.5 to 1.5 mm, with a bevel angle of 50 to 150 (see Figure #1).
- 4 Individual Wafer Orientation "Special" Requirements
  - 4.1 360Y LiTaO3
    - 4.1.1 Orientation --  $360 Y \pm 0.50$
    - 4.1.2 Primary flat direction -- X-axis.
    - 4.1.3 Secondary flat - none
  - 4.2 X-axis LiTaO3
    - 4.2.1 Orientation -- X-axis  $\pm 0.50$
    - 4.2.2 Primary flat direction --  $112.20$  in Y-axis.

**CHINA NATIONAL SCIENTIFIC INSTRUMENTS & MATERILAS. CORP**

Salse Office: Suite L, 7F, Mansion No 1, GUO DU Development Building, No.182 Chaohui Road, 310014 Hangzhou P.R.China

TEL: 0086-571-85803723 85803731 85803732

FAX: 0086-571-85803724

E-mail: sales@csimc-freqcontrol.com thwu@mail.hz.zj.cn



4.2.3 Secondary flat -- None.

## 5 Package

5.1 Wafers are packaged in plastic containers (25 wafers each) which are individually sealed in plastic bags, and are boxed in cardboard with 8 or less containers. Any empty space shall be filled with packing peanuts and at least 4 inches of foam between the inner and outer boxes.

5.2 Wafer supplier must maintain the records by lot number for material shipped to customer to this specification. The records must include all QC data for measurable parameters of the samples inspected. The records are to be available to customer for a period of one year from date of shipment of the product.

5.3 Each package of 25 wafers must be marked with information required by purchasing and receiving: Wafer's name, wafer orientation, wafer diameter, lot number, inspector's number and date. Each outer box must be marked which side is up, do not stack, fragile, and have two shock watch label attached to opposite sides, and also be labeled with the following:

5.3.1 Supplier name and address

5.3.2 Lot number

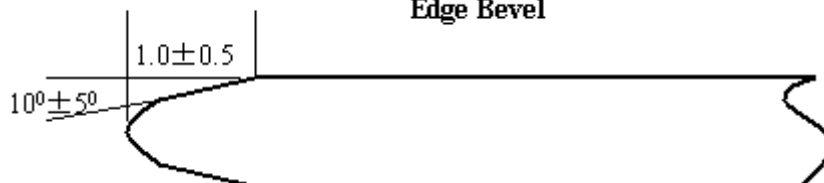
5.3.2 Customer's name and address

5.3.3 Customer's part number, if required

5.3.4 Date boxed

**Figure 1#**

**Edge Bevel**



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Figure 2#

LiTaO<sub>3</sub> Wafer Secondary Flat Locations By Cut Angle

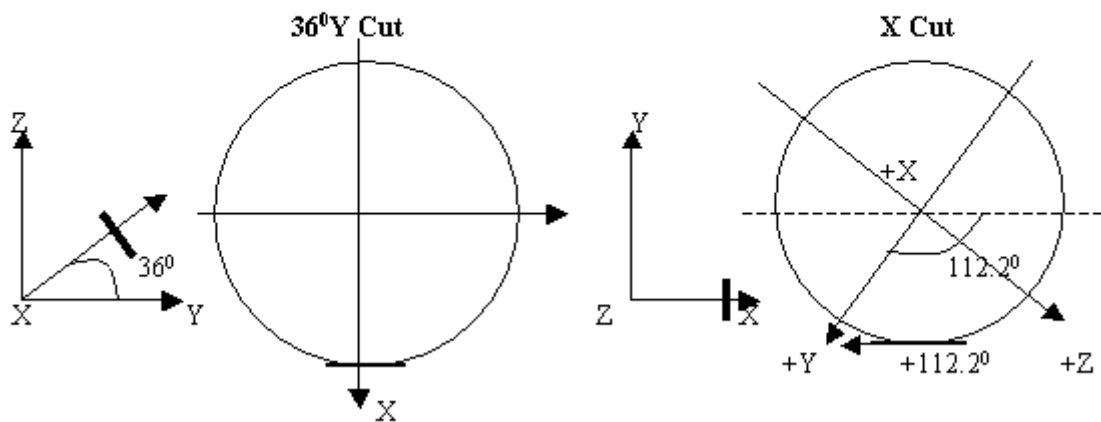


Figure 3#

Bow is the maximum height difference between any two point on the center line.

Wafer may not be in a vacuum state.

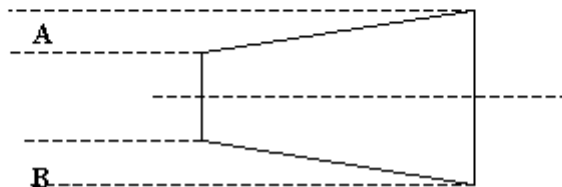
$$BOW = B \quad B > C$$



Figure 4#

Taper is the absolute difference between maximum and minimum thickness of a test sample encountered during a thickness scan or series of point thickness measurements.

$$TAPER = A + B$$



**Figure 5#**

**Top surface flatness is the maximum height difference between any two points on the wafer surface.**

**The wafer may be in a vacuum state.**

**If  $A > B$  then surface flatness = A.**

